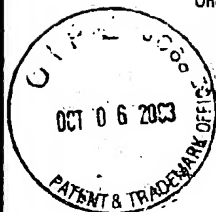


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of
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Complete if Known

Application Number	10/085,759
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Filing Date	28 February 2002
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First Named Inventor	Michel Luc Cote
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Group Art Unit	1752
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Examiner Name	Unassigned	ROS9500
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Attorney Docket Number	NMTI 1002-6
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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**Examiner
Signature**

E. Zúñiga

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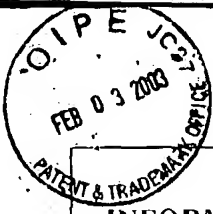
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INFORMATION DISCLOSURE
CITATION

PTO-1449

Atty. Docket No.
NMTI 1002-6Serial No.
10/085,759Applicant
CÔTÉ, Michel LucFiling Date
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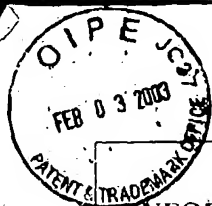
U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>EC</i>	6,420,074 B2	7/16/2002	Wang et al.	430	5	12/7/2000
	6,436,590 B2	8/20/2002	Wang, et al.	430	5	4/20/2001
	2002/0083410 A1	6/27/2002	Wu, et al.	716	19	12/5/2001
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	2002/0129327 A1	9/12/2002	Pierrat, et al.	716	19	11/15/2001
	2002/0136964 A1	9/26/2002	Pierrat	430	5	3/23/2001
	2002/0142231 A1	10/3/2002	Kling, et al.	430	5	4/25/2001
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<i>EC</i>	2002/0155363 A1	10/24/2002	Cote, et al.	430	5	6/7/2002

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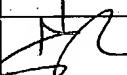
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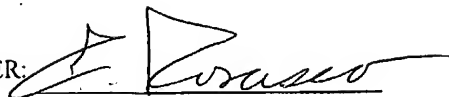
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		Applicant CÔTÉ, Michel Luc	Group 1756
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Cooke, M., "OPC/PSM Designs For Poly Gate Layers", European Semiconductor, Vol. 22, No. 7, pp. 57-59, July 2000.		
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INFORMATION DISCLOSURE CITATION PTO-1449		Att. Docket No. NMTI 1002-6		Serial No. 10/085,759		
		Applicant CÔTÉ, Michel Luc		Group 1752 Not Yet Assigned		
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<i>FL</i>	5,302,477	4/12/1994	Dao, et al.	430	5	8/21/1992
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	5,324,600	6/28/1994	Jinbo, et al.	430	5	7/7/1992
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	5,527,645	6/18/1996	Pati, et al.	430	5	11/17/1994
	5,537,648	7/16/1996	Liebmann, et al.	395	500	8/15/1994
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	5,573,890	11/12/1996	Spence	430	311	7/18/1994
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	5,636,131	6/3/1997	Liebmann, et al.	364	490	5/12/1995
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<i>FL</i>	5,923,566	6/13/1999	Galan, et al.	364	489	3/25/1997

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		CÔTÉ, Michel Luc				
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	6,057,063	5/2/2000	Liebmann, et al.	430	5	4/14/1997
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	6,251,549 B1	6/26/2001	Levenson	430	11	10/28/1999
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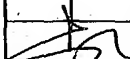
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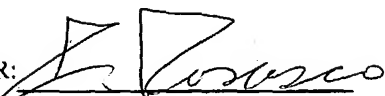
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		Applicant CÔTÉ, Michel Luc	Group <u>1752</u> Not Yet Assigned
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
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		Applicant CÔTÉ, Michel Luc	Group 1752 Not Yet Assigned
		Filing Date 2/28/2002	
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Date Considered: 2/4/04

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No.	Serial No.
	NMTI 1002-6	10/085,759
	Applicant	
	CÔTÉ, Michel Luc	
	Filing Date	Group
	2/28/2002	1752
		Not Yet Assigned

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EXAMINER: A. RosascoDate Considered: 2/4/04

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INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NMTI 1002-6	Serial No. 10/085,759
		Applicant CÔTÉ, Michel Luc	Group 1752 Not Yet Assigned
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
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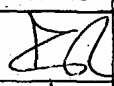
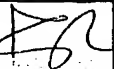
INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No.	Serial No.
		NMTI 1002-6	10/085,759
		Applicant	
		CÔTÉ, Michel Luc	
		Filing Date	Group
		2/28/2002	1752 Not Yet Assigned
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
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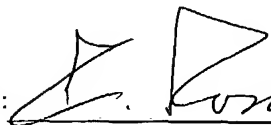
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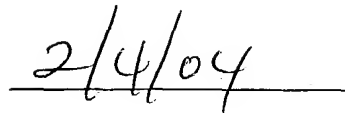
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